

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	42	(III near2 nitride or gan or algan or ingan or gallium near nitride) same (fielo or facet near initiat\$4 near (log or elo or epitaxial near2 overgrowth or lateral near overgrowth))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 15:11
L2	414	(III near2 nitride or gan or algan or ingan or gallium near nitride) and (flat or flattened or flattening or flatten) near3 (interface or growth or interfacial)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 15:15
L3	14	(US-20030037722-\$ or US-20020046693-\$ or US-20030017685-\$ or US-20030070607-\$ or US-20020197825-\$ or US-20020081763-\$ or US-20030134493-\$ or US-20050142682-\$).did. or (US-6447604-\$ or US-6596079-\$ or US-6773504-\$ or US-6921678-\$).did. or (EP-1246233-\$).did. or (JP-2002343728-\$).did.	US-PGPUB; USPAT; EPO; JPO	OR	ON	2007/06/13 15:12
L4	48	(III near2 nitride or gan or algan or ingan or gallium near nitride) and (flat or flattened or flattening or flatten) near3 (interface or growth or interfacial) and (defect or pit or recess or recessed or cavity) near3 (buried or burying or overgrow\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 15:19
L5	245	(III near2 nitride or gan or algan or ingan or gallium near nitride) and (defect or pit or recess or recessed or cavity) near3 (buried or burying or overgrow\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 15:27
L7	88	(III near2 nitride or gan or algan or ingan or gallium near nitride) and ((defect or pit or recess or recessed or cavity) near3 (buried or burying or overgrow\$4) or flat\$4 near2 (growth or epitaxial) near2 (interface or interfacial or surface)) and (impurity or dopant or doping) near2 (concentration or density or uniform\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 15:36
L8	174	(III near2 nitride or gan or algan or ingan or gallium near nitride) and (impurity or dopant or doping) near2 (concentration or density) near3 (uniform\$4 or gradient)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 15:56

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L9	147	257/E29.005.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 16:00
L10	105	257/E29.09.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 16:07
L11	4	257/E29.106.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 16:07
L12	41	257/E29.108.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 16:13
L13	292	257/E29.109.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 16:13
L15	51	257/E21.1.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 16:17
S41	125	(III near2 nitride or gan or algan or ingan or gallium near nitride) near6 (doped or doping or dopant or impurity) same (hvpe or halide near vpe or halide near vapor near phase near epitaxy) and (doping or dopant or impurity or doped or silicon or magnesium or p or n) near6 (uniform\$4 or consisten\$4 or constant or within or chang\$4 or unvary\$4 or nonvary\$4 or identical or similar)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 08:09

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S42	141	(III near2 nitride or gan or algan or ingan or gallium near nitride) near6 (doped or doping or dopant or impurity) same (hvpe or halide near vpe or halide near vapor near phase near epitaxy) and (doping or dopant or impurity or doped or silicon or magnesium or p or n or carrier or hole or electron) near6 (uniform\$4 or consisten\$4 or constant or within or chang\$4 or unvary\$4 or nonvary\$4 or identical or similar)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 08:20
S43	74	(III near2 nitride or gan or algan or ingan or gallium near nitride) near6 (doped or doping or dopant or impurity) same (hvpe or halide near vpe or halide near vapor near phase near epitaxy) and (gas or carrier or ambient) near4 (h or hydrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 08:26
S45	101	(III near2 nitride or gan or algan or ingan or gallium near nitride) same (uniform\$4 or variance or varying or consisten\$4) near3 (doping or (dopant or carrier or hole or electron or impurity) near (concentration or density))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 08:27
S46	221	(III near2 nitride or gan or algan or ingan or gallium near nitride) near6 (doped or doping or dopant or impurity) same (hvpe or halide near vpe or halide near vapor near phase near epitaxy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 08:34
S47	78	(III near2 nitride or gan or algan or ingan or gallium near nitride) near10 (mocvd or hvpe or omvpe or cvd or growth or deposition) near8 (ti or titanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 08:45
S48	360	257/76.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 08:58
S49	392	257/615.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 09:25

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S50	194	257/631.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 09:38
S51	152	117/89.ccls. and (gan or algan or ingan or inalgan or gallium near nitride or ga near n or iii near nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 10:01
S52	272	117/93.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 10:06
S53	54	117/102.ccls. and (gan or algan or ingan or inalgan or gallium near nitride or ga near n or iii near nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 10:26
S54	781	117/105.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/13 10:32

Inference Search

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L16	8	((III near2 nitride or gan or algan or ingan or gallium near nitride) same (uniform\$4 or variance or varying or consisten\$4) near3 (doping or dopant or carrier or hole or electron or impurity)).clm.	US-PGPUB	OR	ON	2007/06/13 16:26
L18	9	((III near2 nitride or gan or algan or ingan or gallium near nitride) near2 substrate and substrate near4 (thinned or thinning or ultrathin or self near support\$4 or self near stand\$4)).clm.	US-PGPUB	OR	ON	2007/06/13 16:22
L19	5	((III near2 nitride or gan or algan or ingan or gallium near nitride) and (doping or dopant or impurity or carrier or hole or electron) near4 (concentration or density) near6 (percent or percentage or "%" or cm or "cm.sup.-3")).clm.	US-PGPUB	OR	ON	2007/06/13 16:25
L20	22	((III near2 nitride or gan or algan or ingan or gallium near nitride) and (doping or dopant or impurity or carrier or hole or electron) near4 (concentration or density) and (planariz\$4 or polish\$4)).clm.	US-PGPUB	OR	ON	2007/06/13 16:25
L21	55	((III near2 nitride or gan or algan or ingan or gallium near nitride) and (doping or dopant or carrier or hole or electron or impurity) and (hvpe or halide near vpe or halide near vapor near phase near epitaxy)).clm.	US-PGPUB	OR	ON	2007/06/13 16:26
L22	11	((III near2 nitride or gan or algan or ingan or gallium near nitride) and ((defect or pit or recess or recessed or cavity) near3 (buried or burying or overgrow\$4) or flat\$4 near2 (growth or epitaxial) near2 (interface or interfacial or surface))).clm.	US-PGPUB	OR	ON	2007/06/13 16:28

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Search history:

	No.	Database	Search term	Info added since	Results
<input type="checkbox"/>	1	INZZ	(gan OR ingan OR algan OR gallium ADJ nitride) AND (doping OR dopant OR impurity) NEAR (uniform\$ OR variance OR varying OR consisten\$)	unrestricted	29
<input type="checkbox"/>	2	INZZ	(gan OR ingan OR algan OR gallium ADJ nitride) NEAR hvpe	unrestricted	383
<input type="checkbox"/>	3	INZZ	(gan OR ingan OR algan OR gallium ADJ nitride) NEAR hvpe NEAR (defect OR dislocation)	unrestricted	15
<input type="checkbox"/>	4	INZZ	(gan OR ingan OR algan OR gallium ADJ nitride) AND (defect OR pit OR recess OR recessed OR cavity) NEAR (buried OR burying OR overgrow\$)	unrestricted	34
<input type="checkbox"/>	5	INZZ	(gan OR ingan OR algan OR gallium ADJ nitride) AND flat\$ NEAR (growth OR epitaxial) NEAR (interface OR interfacial OR surface)	unrestricted	19
<input type="checkbox"/>	6	INZZ	(gan OR ingan OR algan OR gallium ADJ nitride) AND (doping OR dopant OR impurity) NEAR (uniform\$ OR variance OR varying OR consisten\$) NEAR (density OR concentration)	unrestricted	4
<input type="checkbox"/>	7	INZZ	(gan OR ingan OR algan OR gallium ADJ nitride) AND (doping OR dopant OR impurity) NEAR (uniform\$ OR variance OR varying OR consisten\$) NEAR (top OR bottom OR surface)	unrestricted	0

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